FORM PTO-	TO-1449 U.S. DEPARTMENT OF COMMERCE				Sheet 1 of 1 ATTORNEY DOCKET NO. 1639.1008D Sheet 1 of 1 APPLICATION NO. 10/62573 Unassigned				
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LIST OF COPENDING APPLICATIONS

ATTACHMENT 1(f)

1639.1008D

FIRST NAMED INVENTOR

Naoto FUJISHIMA

FILING DATE

July 24, 2003

ATTACHMENT 1(f)

APPLICATION 10 0 10 0 25 734

Undessigned

GROUP ART UNIT

2822 2823

The following, prior-filed, copending U.S. patent application(s) is/are listed in accordance with the duty of disclosure provisions of 37 CFR § 1.56, so that the Examiner may consider same should he deem any the identified copending application(s) is provided.

It is requested that the Examiner acknowledge his consideration of application(s) below-listed by initialling same in the space provided adjacent each such application and that the Examiner sign and date this form at the bottom thereof to confirm such consideration having been given.

This submission in no way represents an admission that any of the information listed herein constitutes prior art with respect to the subject application and unless and until such prior art status is established, this submission is not a request that the information presented herein be printed on the face of any patent issuing from the subject application in which this information is being filed.

U.S. PATENT APPLICATION DOCUMENTS EXAMINER INITIAL U.S. SERIAL NO. FILING DATE 1 NAME 10/156,641 K.N. May 29, 2002 **ASSIGNEE** Naoto FUJISHIMA Fuji Electric Co., Ltd. 2 3 4 5 6 7 8

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	DATE CONSIDERED
EXAMINER: Initial if reference and ideal	12/08/04
EXAMINER: Initial if reference considered, whether or not citatic citation if not in conformance and not considered. Include copy of	ion is in conformance with MPEP 609; Draw line through this form with next communication to applicant.